Type L # Hits				Search Text	DBs	Time Stamp	Com ment s	Erro r Defin ition	E S
BRS L1 24660 floating adj gate\$1	L1 2466(24660 floating adj ε	floating adj g		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 15:28			0
passiv\$9 same ((silicon adj nitride) or Si3N4 or "Si3N4" or SiN\$1 to or Or Si.sub.3N.sub.4" jor "Si.sub.3 N.sub.4") same (polyimid\$3 or poly-imid\$3 or	L2 1210		passiv\$9 san ((silicon adj or Si3N4 or Si3N4" or Sor "Si3N4" or Sor "Si.sub.3N.sı or "Si.sub.3 N.sub.4") san (polyimid\$3	ne nitride) iN\$1 ub.4" ne or or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:27			0
BRS L3 14 1 and 2	L3 14		1 and 2		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:08			0
BRS L4 2641 (polyimid\$3 or poly-imid\$3 or (poly adj imid\$3))	2641		passiv\$9 witl (polyimid\$3 poly-imid\$3 (poly adj imi	n or or d\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:27			0

	Type L#	Hits	Search Text	DBs	Time	Com ment s	Erro r Defin ition	因 Li S
LS		17	4 and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:27			0
F.6		2416	(flash adj memor\$4) with (EEPROM\$1 or EPROM\$1 or US-PGPUB; (electrical\$4 adj program\$6 adj read IBM_TDB adj only adj memor\$4)) with (non-volat\$6 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 15:28			0
L7		24659	24659 floating adj (gate or US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 15:28	,		0
L8		492	6 and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 15:29			0